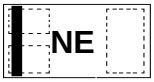
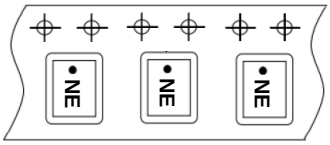
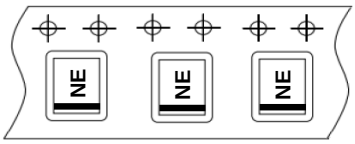
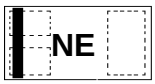
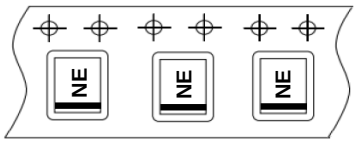
Marking Information

DMN3730UFB-7	 Top View Dot Denotes Drain Side From date code 1527 (YYWW), this changes to:  Top View Bar Denotes Gate and Source Side  
DMN3730UFB-7B	 Top View Bar Denotes Gate and Source Side NE = Part Marking Code 

Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±8	
Continuous Drain Current	V_{GS} = 4.5V	(Note 6)	I_D	0.91	A
		T_A = +70°C (Note 6)		0.73	
		(Note 5)		0.75	
Pulsed Drain Current		(Note 7)	I_{DM}	3	A

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)	P_D	0.69	W
	(Note 5)		0.47	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	180	°C/W
	(Note 5)		258	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	V_{GS} = 0V, I_D = 10µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	-	-	1	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	3	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	0.45	-	0.95	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance (Note 8)	$R_{DS\ (ON)}$	-	-	460	mΩ	V_{GS} = 4.5V, I_D = 200mA
				560		V_{GS} = 2.5V, I_D = 100mA
				730		V_{GS} = 1.8V, I_D = 75mA
Forward Transfer Admittance	$\|Y_{fs}\|$	40	-	-	mS	V_{DS} = 3V, I_D = 10mA
Diode Forward Voltage (Note 8)	V_{SD}	-	0.7	1.2	V	V_{GS} = 0V, I_S = 300mA
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	-	64.3	-	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	6.1	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	4.5	-	pF	
Gate Resistance	R_g	-	70	-	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	-	1.6	-	nC	V_{GS} = 4.5V, V_{DS} = 15V, I_D = 1A
Gate-Source Charge	Q_{gs}	-	0.2	-	nC	
Gate-Drain Charge	Q_{gd}	-	0.2	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	3.5	-	ns	V_{DS} = 10V, I_D = 1A V_{GS} = 10V, R_G = 6Ω
Turn-On Rise Time	t_r	-	2.8	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	38	-	ns	
Turn-Off Fall Time	t_f	-	13	-	ns	

Notes:
5. For a device surface mounted on a minimum recommended pad layout of an FR4 PCB, in still air conditions; the device is measured when operating in steady-state condition.
6. Same as Note 5, except the device measured at t ≤ 10 seconds.
7. Same as Note 5, except the device is pulsed at duty cycle of 1% for a pulse width of 10µs.
8. Measured under pulsed conditions to minimize self-heating effect. Pulse width ≤ 300µs; duty cycle ≤ 2%.
9. For design aid only, not subject to production testing.

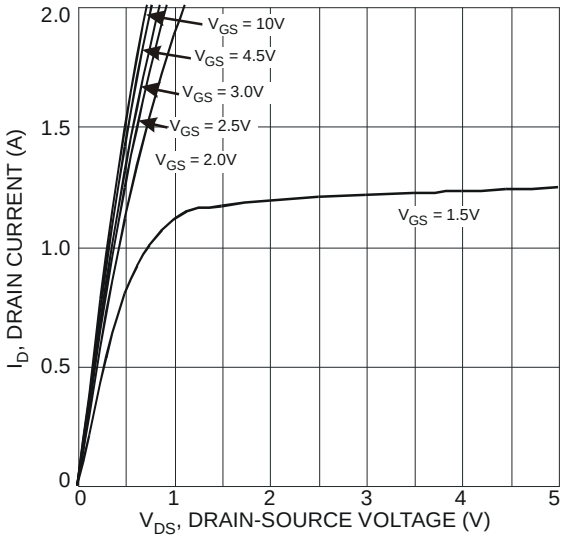


Fig. 1 Typical Output Characteristic

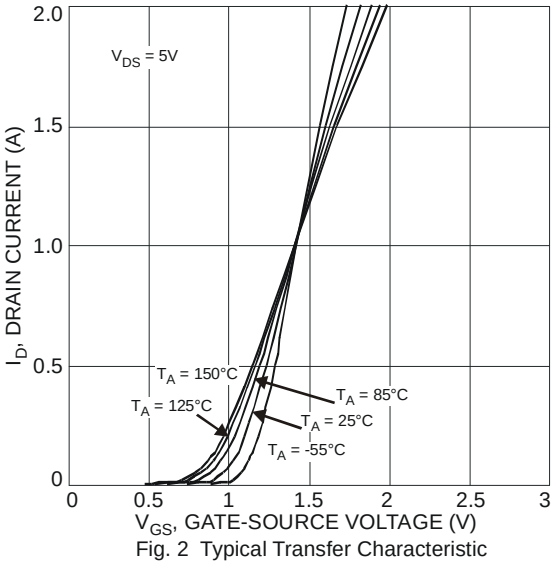


Fig. 2 Typical Transfer Characteristic

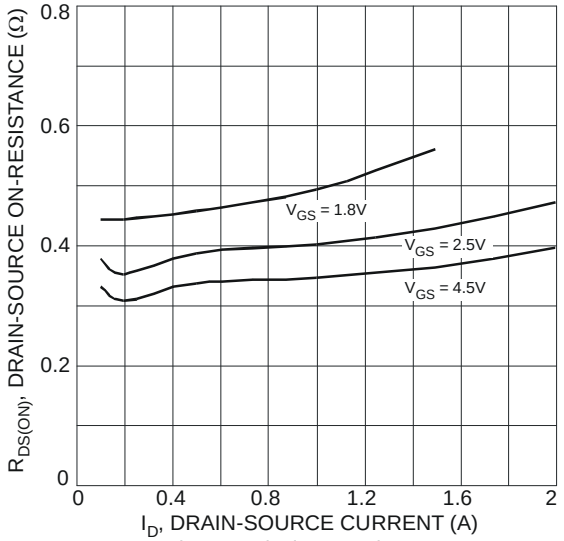


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

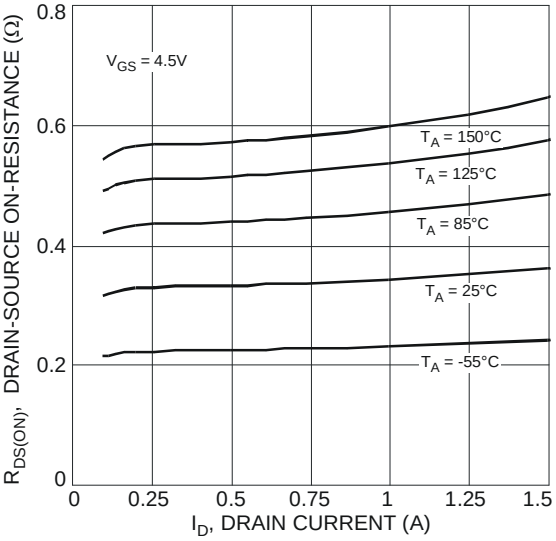


Fig. 4 Typical On-Resistance
vs. Drain Current and Temperature

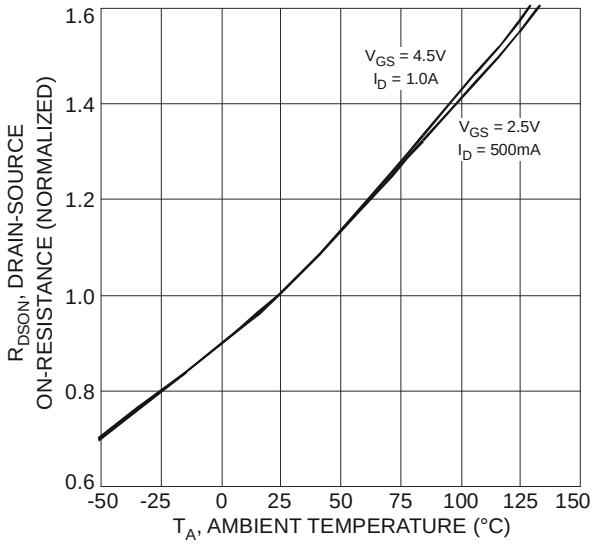


Fig. 5 On-Resistance Variation with Temperature

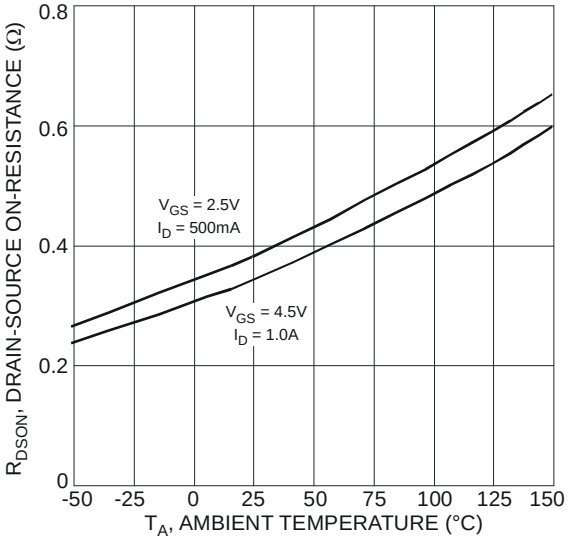


Fig. 6 On-Resistance Variation with Temperature

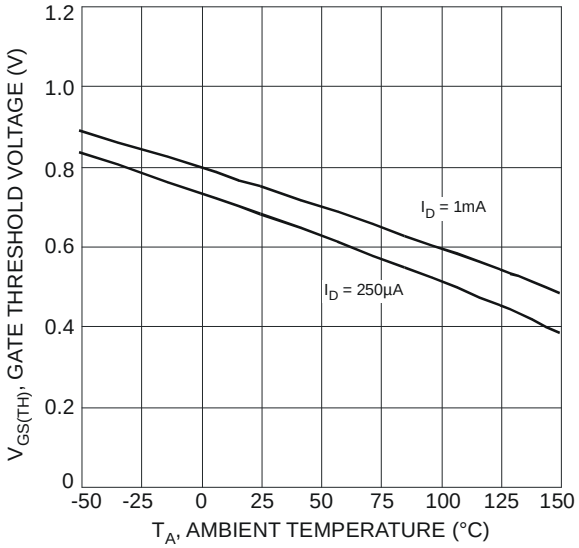


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

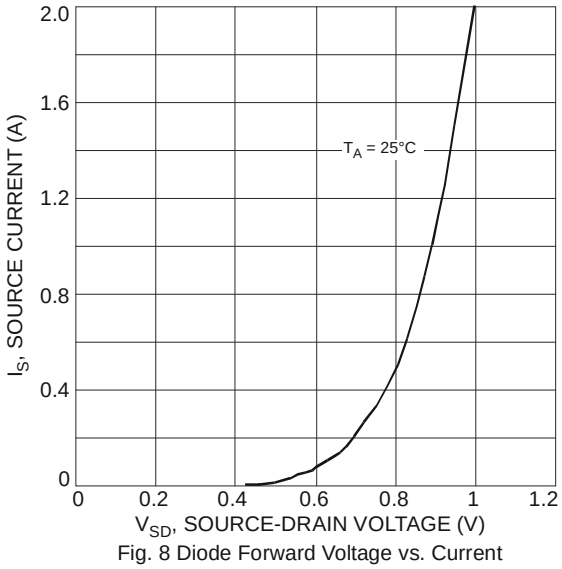


Fig. 8 Diode Forward Voltage vs. Current

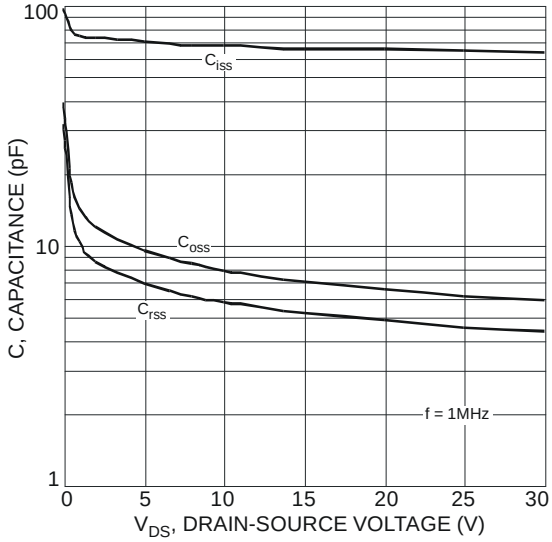


Fig. 9 Typical Total Capacitance

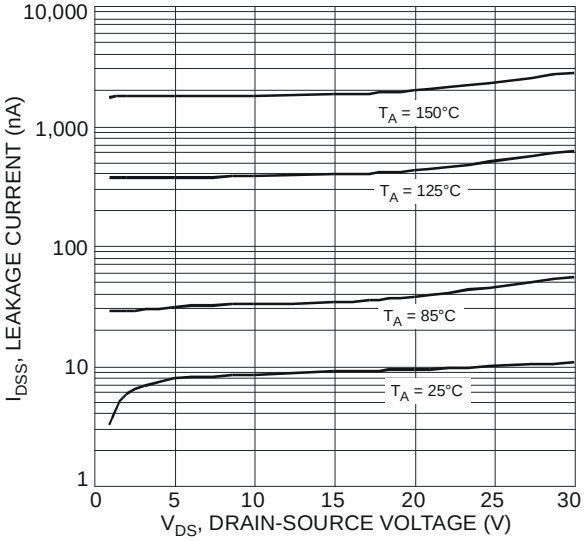


Fig. 10 Typical Leakage Current
vs. Drain-Source Voltage

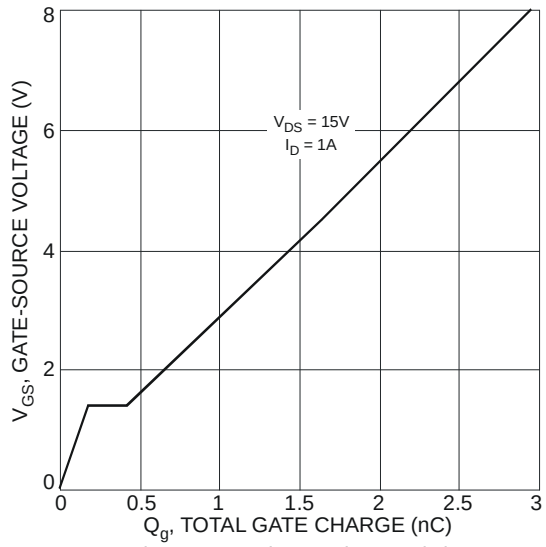


Fig. 11 Gate-Charge Characteristics

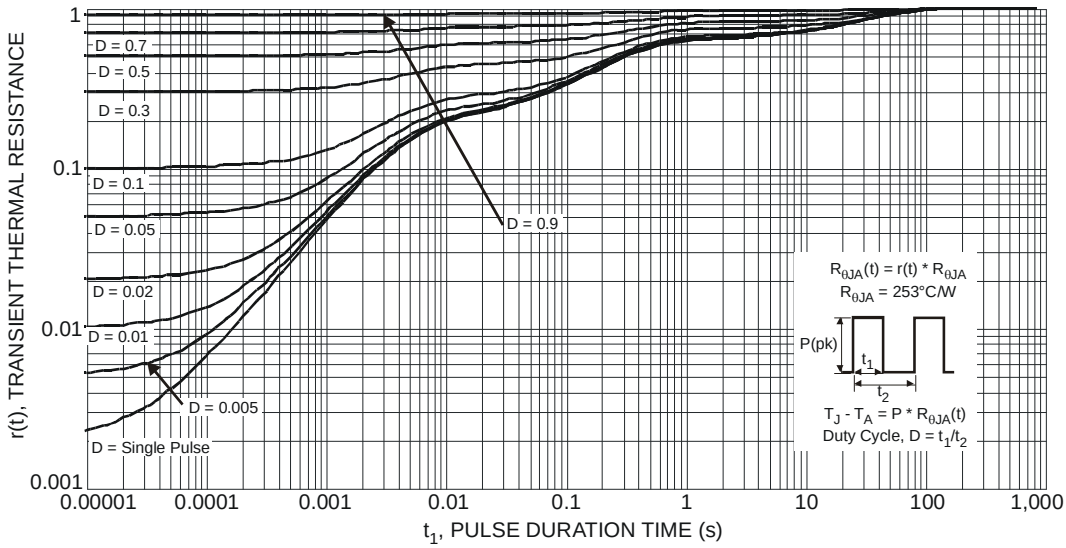
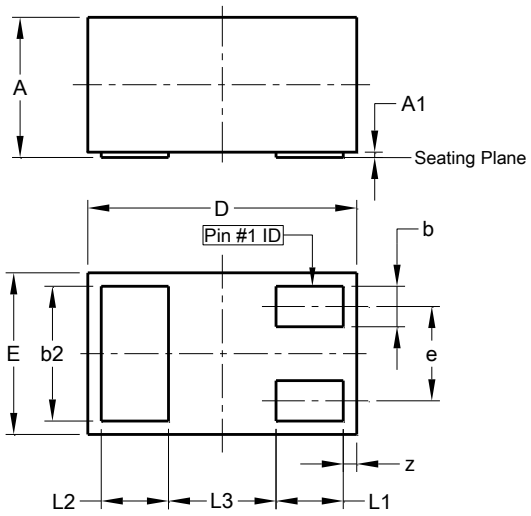


Fig. 12 Transient Thermal Response

Package Outline Dimensions

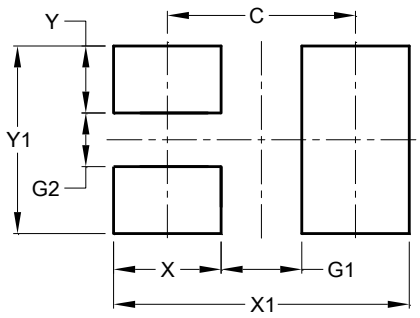
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X1-DFN1006-3			
Dim	**Min**	**Max**	**Typ**
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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